

**CMNDM8001**  
**SURFACE MOUNT**  
**P-CHANNEL**  
**ENHANCEMENT-MODE**  
**SILICON MOSFET**



[www.centralsemi.com](http://www.centralsemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMNDM8001 is an Enhancement-mode P-Channel MOSFET, manufactured by the P-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low  $r_{DS(ON)}$  and Low Threshold Voltage.

**FEMTOmini™**



**SOT-953 CASE**

- Device is **Halogen Free** by design

**APPLICATIONS:**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

**MARKING CODE: BC**

**FEATURES:**

- Low 0.5mm Package Profile
- Low  $r_{DS(ON)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, FEMTOmini™ 1.0 x 0.8mm, SOT-953 Surface Mount Package

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	10	V
Continuous Drain Current (Steady State)	$I_D$	100	mA
Continuous Drain Current	$I_D$	200	mA
Power Dissipation	$P_D$	250	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

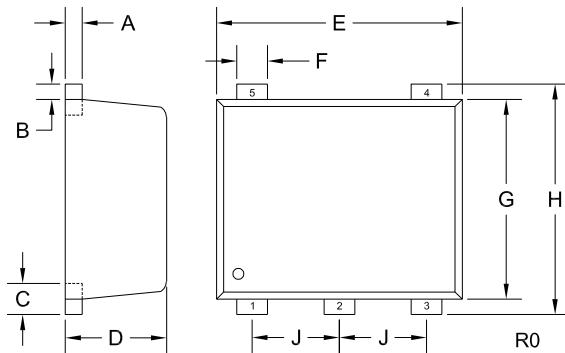
<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
$I_{GSSF}, I_{GSSR}$	$V_{GS}=10\text{V}, V_{DS}=0$			1.0	$\mu\text{A}$
$I_{DSS}$	$V_{DS}=20\text{V}, V_{GS}=0$			1.0	$\mu\text{A}$
$BV_{DSS}$	$V_{GS}=0, I_D=100\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.6		1.1	V
$r_{DS(ON)}$	$V_{GS}=4.0\text{V}, I_D=10\text{mA}$			8.0	$\Omega$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=10\text{mA}$			12	$\Omega$
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=1.0\text{mA}$			45	$\Omega$
$g_{fs}$	$V_{DS}=10\text{V}, I_D=100\text{mA}$	100			$\text{mS}$
$C_{rss}$	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
$C_{iss}$	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		45		pF
$C_{oss}$	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
$t_{on}$	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$		35		ns
$t_{off}$	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$		80		ns

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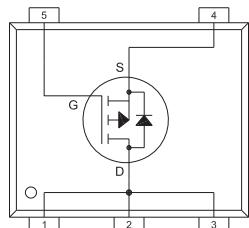
**SOT-953 CASE - MECHANICAL OUTLINE**



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.002	0.006	0.050	0.150
B	0.002	0.006	0.050	0.150
C	0.005	0.007	0.125	0.175
D	0.016	0.020	0.400	0.500
E	0.037	0.041	0.950	1.050
F	0.004	0.008	0.100	0.200
G	0.030	0.033	0.750	0.850
H	0.037	0.041	0.950	1.050
J	0.014		0.350	

SOT-953 (REV: R0)

**PIN CONFIGURATION**



**LEAD CODE:**

- 1) Drain
- 2) Drain
- 3) Drain
- 4) Source
- 5) Gate

**MARKING CODE: BC**

R1 (25-January 2010)